



Ⓢ Pending

Active

.. L12: (15089) (wordline or word-line or (word adj line)) near5 decod\$4

--- L13: (404981) latch\$4

L 14: (689215) invert \$4

☞ L 15: (983) 12 with 13

☛ L 16: (59) 14 with 15

- L22: (2162) 12 same 13

- L23: (250) 14 same 22

☞ L24: (194) 23 not 16

L25: (6106) 365/230.06

L26: (2713) 365/230.08

✉ L27: (3300) 365/189.09

--- L28: (2234) 365/189.11

--L29: (349) 326/105

L30: (262) 326/108

✓ L32: (9) 22 and 30

...L34: (19) 22 and 29

☞ L33: (405) 22 and 25

☛ L34: (268) 22 and 26

☞ L35: (151) 22 and 27

L36: (113) 22 and 28

☛ L40: (104) 12 and 29

• L41: (67) 12 and 30

☛ L42: (56) (ABEDIFAI)

Failed

Seam	Lat	Index	Group	Pos
------	-----	--------------	-------	-----

DB: US-PGPUB;USPAT;EPO;JPO;DERWENT;IBM_TDB

Default operator: **OR**

7. Pledge

☒ Highlight all the terms in class

BR5 form IS&R form Image Text HTML

	U	1	2	Inventor	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval Cl	S	C	P	9	10	11
1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	Jun; Dong S. et al.	US 5412331 A	19950502	14	Word line driving circuit of a semiconductor memory device	326/105	326/421; 326/83;		<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US
2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	Jeong; Jae-Hong	US 5862098 A	19990119	13	Word line driver circuit for semiconductor memory device	365/230.06	365/230.03		<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US
3	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	Kohno; Fumihiro	US 6044035 A	20000328	31	Semiconductor memory device having level-shifted precharge	365/230.06	366/189.09; 366/189.11		<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US
4	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	Kohno; Fumihiro	US 6538955 B2	20030325	17	Semiconductor integrated circuit for which high voltage c	365/230.06	326/105		<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US

[Hits](#)
[Details](#)
[HTML](#)

Ready

NUM: